

DIODE ARRAY PRODUCT SPECIFICATION

MONOLITHIC AIR ISOLATED DIODE ARRAY

FEATURES:

- HERMETIC CERAMIC PACKAGE
- $B_V > 60V$ at $10\mu A$
- $I_r < 100nA$ at $40V$
- $C < 8.0 pF$

Absolute Maximum Ratings:

Symbol	Parameter	Limit	Unit
$V_{BR}(R) *1 *2$	Reverse Breakdown Voltage	60	Vdc
$I_O *1 *3$	Continuous Forward Current	300	mAdc
$I_{FSM} *1$	Peak Surge Current ($t_p = 1/120 s$)	500	mAdc
$PT1 *4$	Power Dissipation per Junction @ $25^\circ C$	400	mW
$PT2 *4$	Power Dissipation per Package @ $25^\circ C$	600	mW
T_{op}	Operating Junction Temperature Range	-65 to +150	$^\circ C$
T_{stg}	Storage Temperature Range	-65 to +200	$^\circ C$

NOTE 1: Each Diode

NOTE 2: Pulsed: $PW = 100ms$ max.; duty cycle $\leq 20\%$

NOTE 3: Derate at $2.4mW/^\circ C$ above $+25^\circ C$

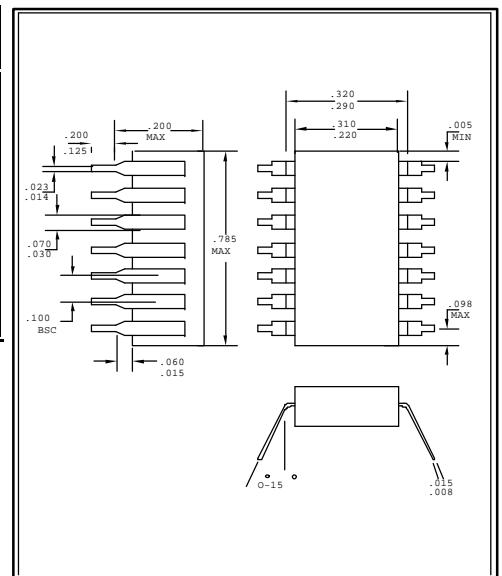
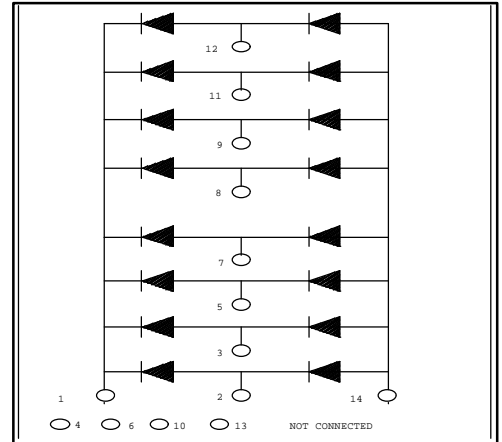
NOTE 4: Derate at $4.0mW/^\circ C$ above $+25^\circ C$

Electrical Characteristics (Per Diode) @ $25^\circ C$ unless otherwise specified

Symbol	Parameter	Conditions	Min	Max	Unit
V_{f1}	Forward Voltage	$I_f = 100mA$ *1		1	Vdc
V_{f2}	Forward Voltage	$I_f = 500mA$ *1		1.5	Vdc
I_{R1}	Reverse Current	$V_R = 40 Vdc$		0.1	μA
C_t	Capacitance (pin to pin)	$V_R = 0 Vdc$; $f = 1 MHz$		8.0	pF
t_{fr}	Forward Recovery Time	$I_f = 500mA$		40	ns
t_{rr}	Reverse Recovery Time	$I_f = I_R = 200mA$, $i_{rr} = 20mA$, $R_L = 100 ohms$		20	ns

NOTE 1: Pulsed: $PW = 300\mu s \pm 50\mu s$, duty cycle $\leq 2\%$, $90\mu s$ after leading edge

Sertech reserves the right to make changes to any product design, specification or other information at any time without prior notice.



PACKAGE OUTLINE